

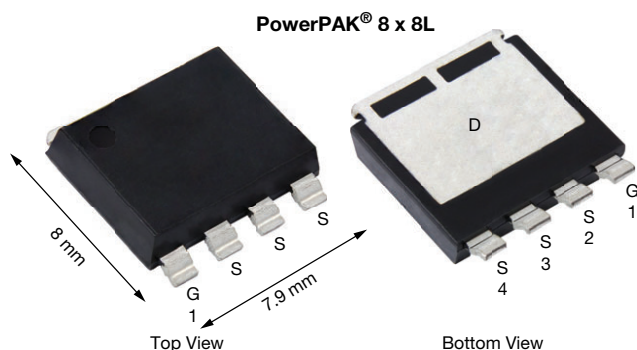
Automotive N-Channel 80 V (D-S) 175 °C MOSFET



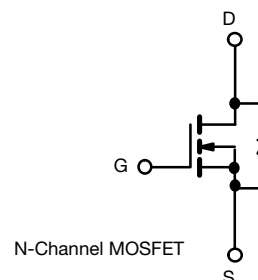
RoHS
COMPLIANT
HALOGEN
FREE

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Thin 1.9 mm height
- Material categorization
for definitions of compliance please see
www.vishay.com/doc?99912



PRODUCT SUMMARY	
V _{DS} (V)	80
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.0023
I _D (A)	245
Configuration	Single
Package	PowerPAK 8 x 8L



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	80	V
Gate-source voltage		V _{GS}	± 20	
Continuous drain current	T _C = 25 °C	I _D	245	A
	T _C = 125 °C		141	
Continuous source current (diode conduction)		I _S	245	
Pulsed drain current ^a		I _{DM}	770	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	58	mJ
		E _{AS}	168	
Maximum power dissipation	T _C = 25 °C	P _D	357	W
	T _C = 125 °C		119	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^c			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^b	R _{thJA}	40	°C/W
Junction-to-case (drain)		R _{thJC}	0.42	

Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257)

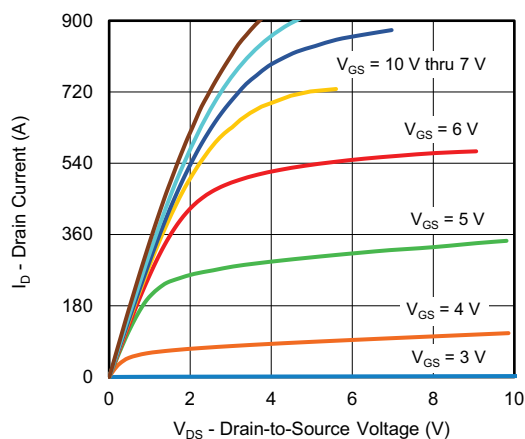
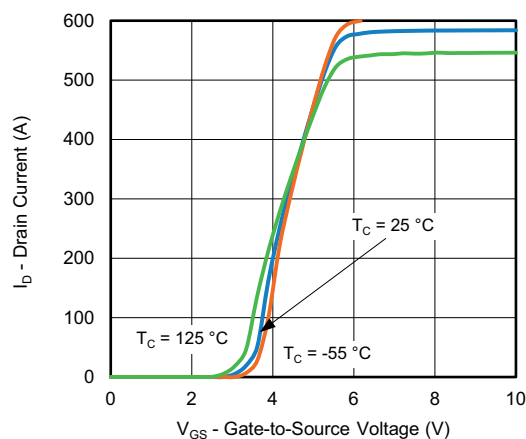
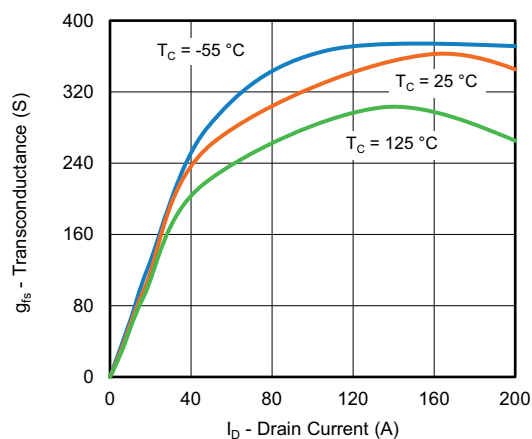
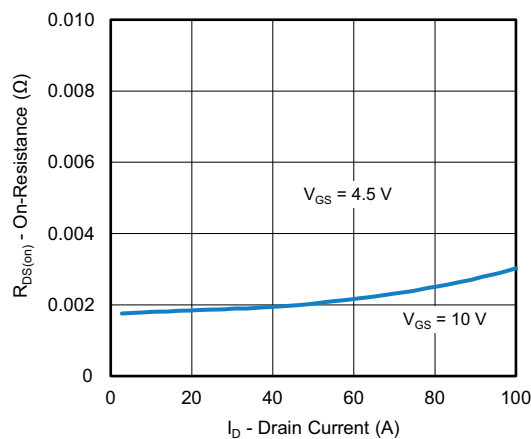
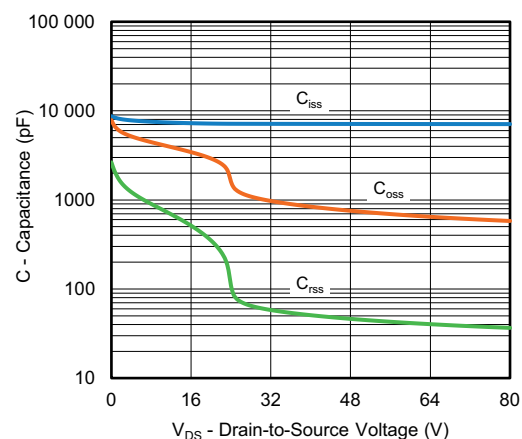
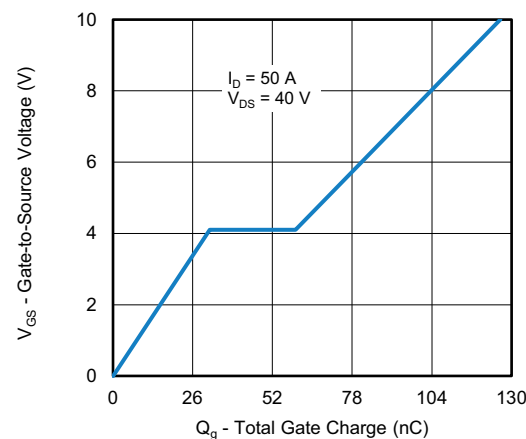


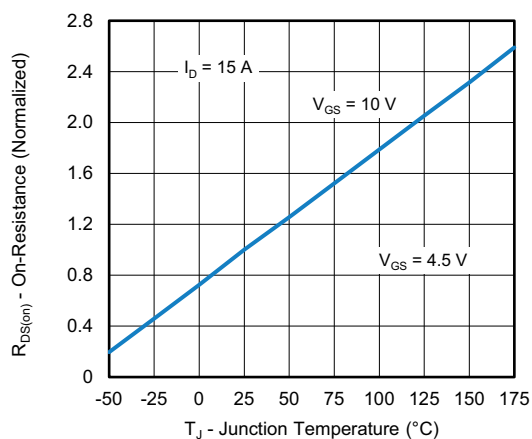
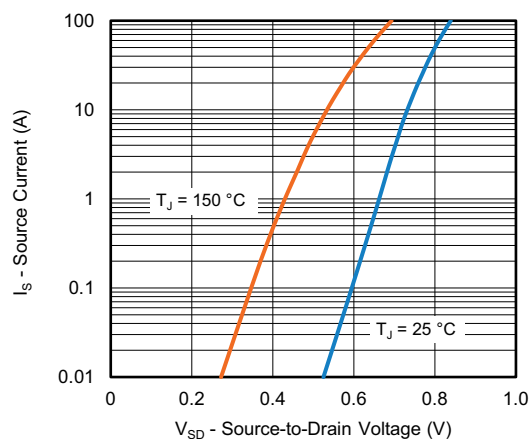
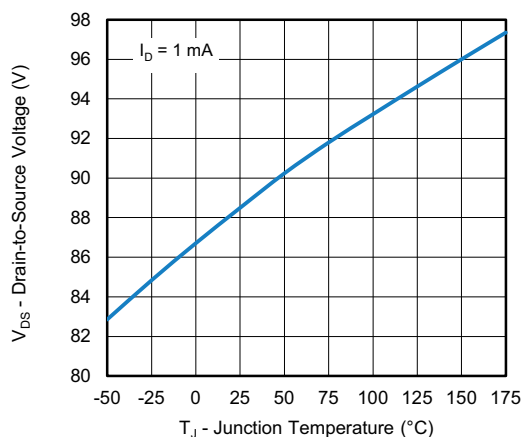
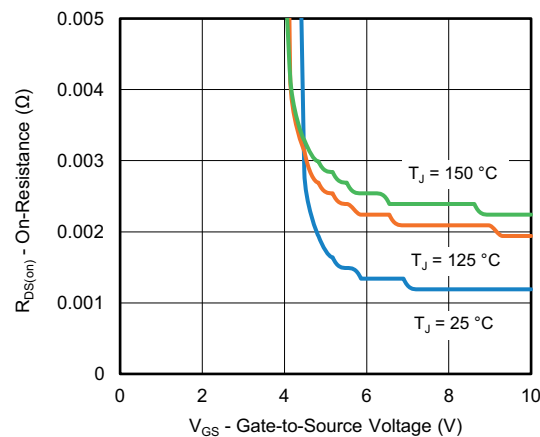
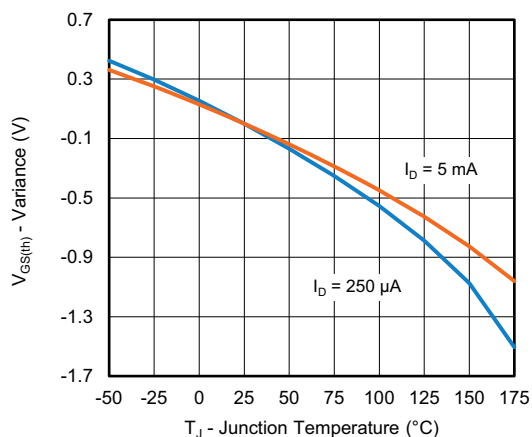
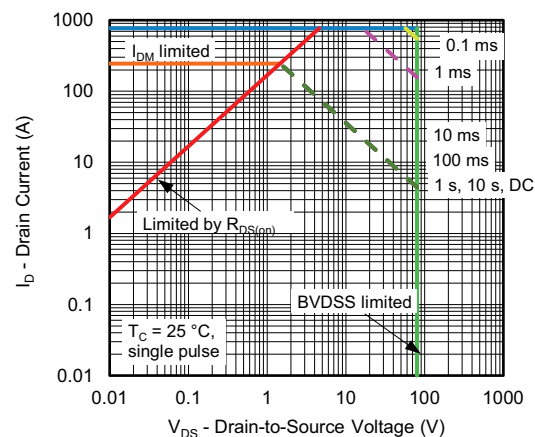
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		80	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.5	3	3.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 80 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 80 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 80 V, T _J = 175 °C	-	-	500	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	50	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A	-	0.0019	0.0023	Ω
		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0047	
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0060	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A		-	90	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	7537	10 552	pF
Output capacitance	C _{oss}			-	1182	1655	
Reverse transfer capacitance	C _{rss}			-	55	77	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 40 V, I _D = 50 A	-	123	185	nC
Gate-source charge ^c	Q _{gs}			-	36	-	
Gate-drain charge ^c	Q _{gd}			-	26	-	
Gate resistance	R _g	f = 1 MHz		0.6	1.3	2	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 40 V, R _L = 4 Ω, I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		-	22	33	ns
Rise time ^c	t _r			-	21	32	
Turn-off delay time ^c	t _{d(off)}			-	53	80	
Fall time ^c	t _f			-	16	24	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	770	A
Forward voltage	V _{SD}	I _F = 40 A, V _{GS} = 0 V		-	0.7	1.2	V
Body diode reverse recovery time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs		-	63	126	ns
Body diode reverse recovery charge	Q _{rr}			-	105	210	nC
Reverse recovery fall time	t _a			-	32	-	ns
Reverse recovery rise time	t _b			-	31	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-3.0	-	A

Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

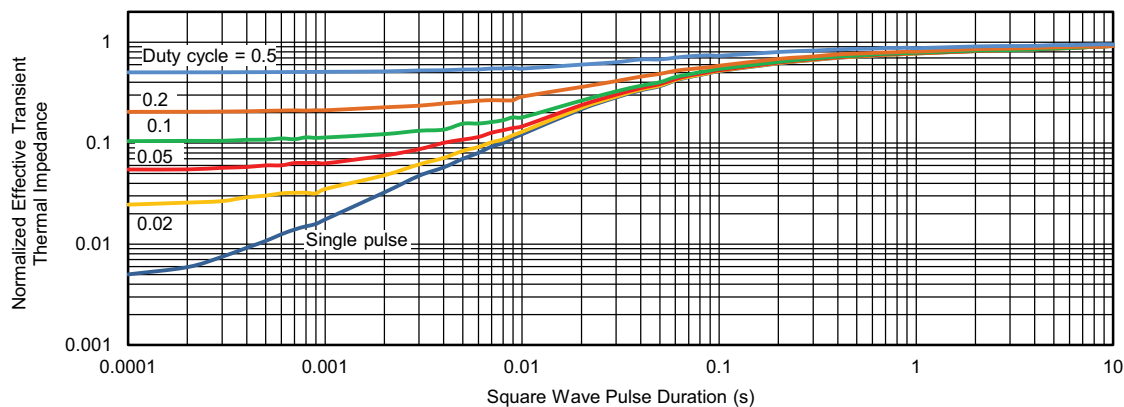
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage

Drain Source Breakdown vs. Junction Temperature

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Safe Operating Area
Note

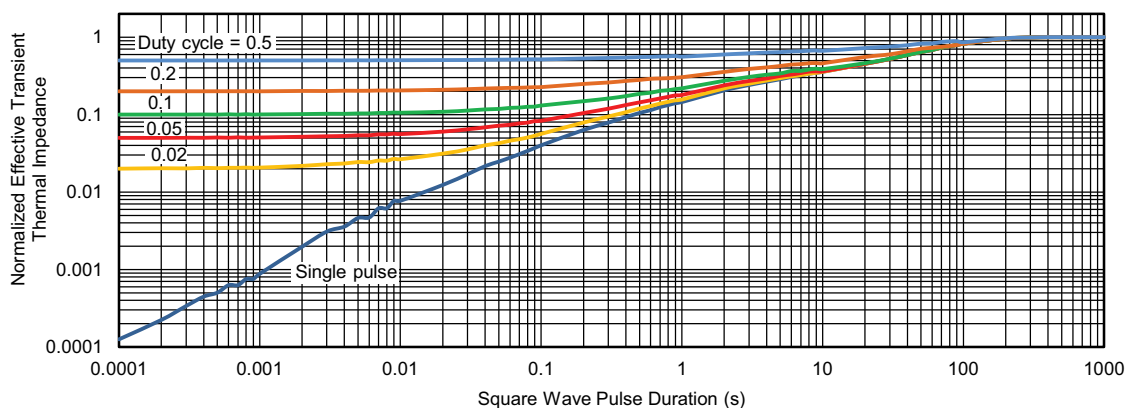
- $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

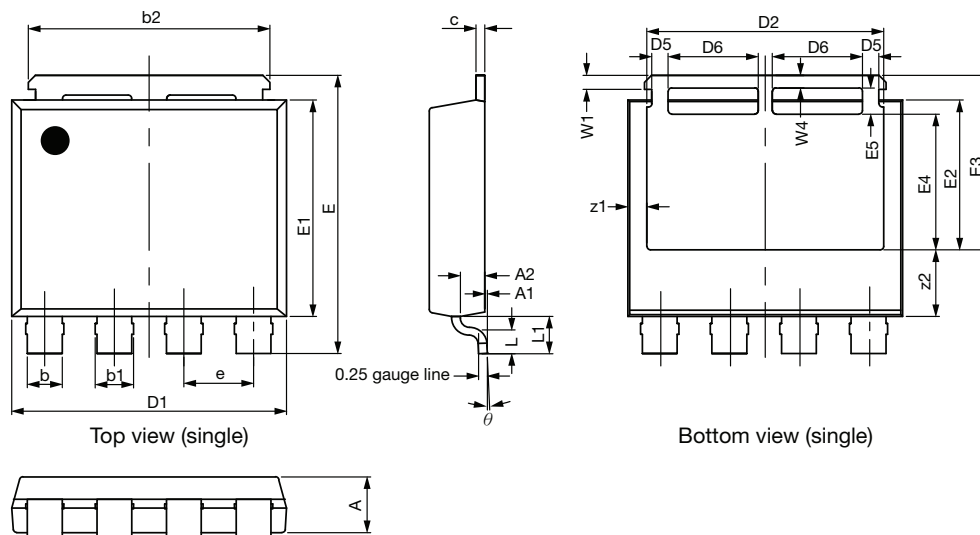


Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

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PowerPAK[®] 8 x 8L BWL Case Outline 2

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.50	1.60	1.70	0.059	0.063	0.067
A1	0.00	-	0.127	0.000	-	0.005
A2	0.655	0.705	0.755	0.026	0.028	0.030
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	6.84	6.94	7.04	0.269	0.273	0.277
c	0.20	0.25	0.30	0.008	0.010	0.012
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D5	0.37	0.47	0.57	0.015	0.019	0.022
D6	2.49	2.59	2.69	0.098	0.102	0.106
e	1.97	2.00	2.03	0.078	0.079	0.080
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	4.21	4.31	4.41	0.166	0.170	0.174
E3	4.92	5.02	5.12	0.194	0.198	0.202
E4	3.80	3.90	4.00	0.150	0.154	0.157
E5	0.65	0.75	0.85	0.026	0.030	0.033
L	0.61	0.68	0.75	0.024	0.027	0.030
L1	1.00	1.07	1.15	0.039	0.042	0.045
W1	0.30	0.40	0.50	0.012	0.016	0.020
W4	0.32	0.37	0.42	0.013	0.015	0.017
z1	0.45	0.55	0.65	0.018	0.022	0.026
z2	1.81	1.91	2.01	0.071	0.075	0.079
θ	0°	-	5°	0°	-	5°
ECN: S19-0643-Rev. B, 05-Aug-2019 DWG: 6073						

Note

- Millimeter will govern



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